	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	282436	257/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	12221	1 and ((thin near film near transistor) or (liquid near crystal near display) or TFT or LCD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	352	2 and pattern near semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	195	3 and source near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L6	2	5 and outer near edge?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L5	64	4 and surround$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L7	1102	(kobayashi-kazuhiro or nakamura-nobuhiro or inoue-kazunori or nakashima-ken or masutani-yuichi or aoki-hironori).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L8	161	7 and ((thin near film near transistor) or (liquid near crystal near display) or TFT or LCD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	7	8 and pattern near semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L10	1	9 and surround$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L11	141686	((thin near film near transistor) or (liquid near crystal near display) or TFT or LCD).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	L12	473	11 and pattern near semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	BRS	L13	277	12 and source near electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
14	BRS	L14	1	13 and outer near edge?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
15	BRS	L15	75	13 and surround$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
16	BRS	L16	19	15 and edge?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	